
2SC4680

Silicon NPN Epitaxial

HITACHI

ADE-208-1118A (Z)
2nd. Edition
Mar. 2001

Application

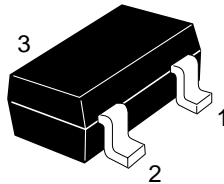
VHF / UHF high frequency switching

Features

- Low Ron and high performance for RF switch.
- Capable of high density mounting.

Outline

MPAK



1. Emitter
2. Base
3. Collector

Note: Marking is "XU-".

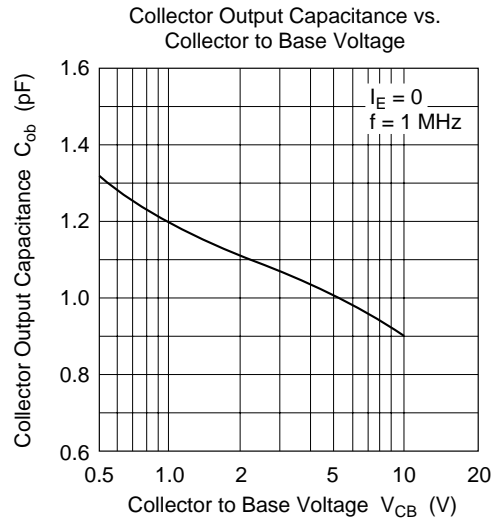
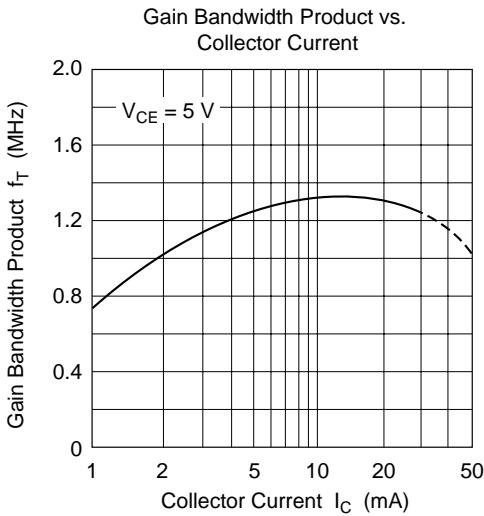
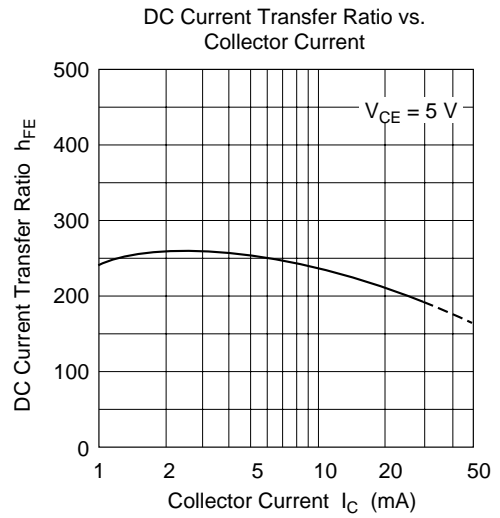
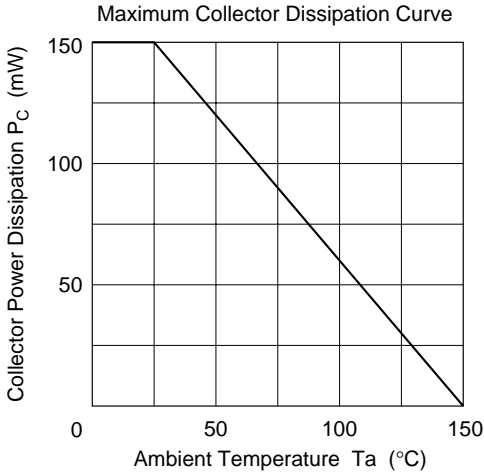
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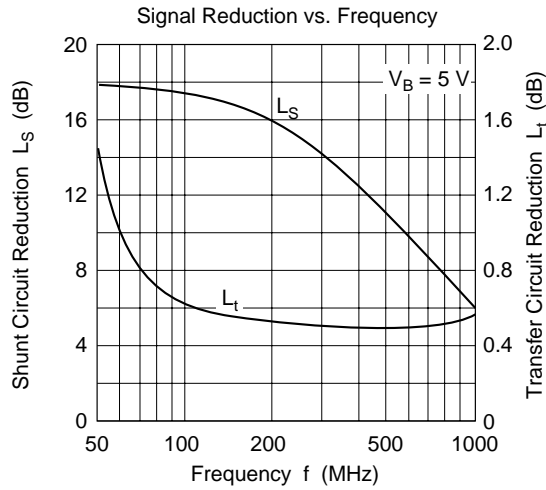
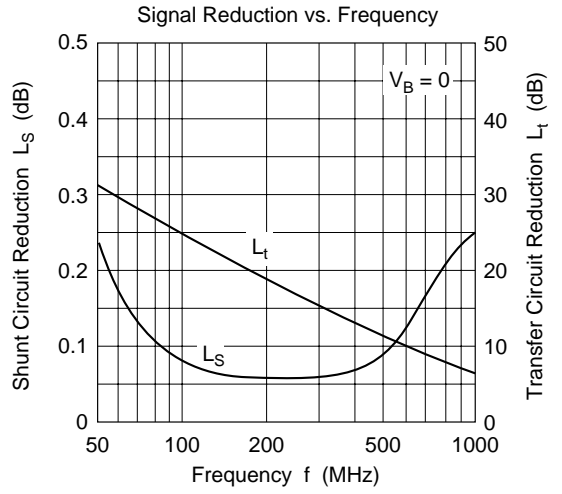
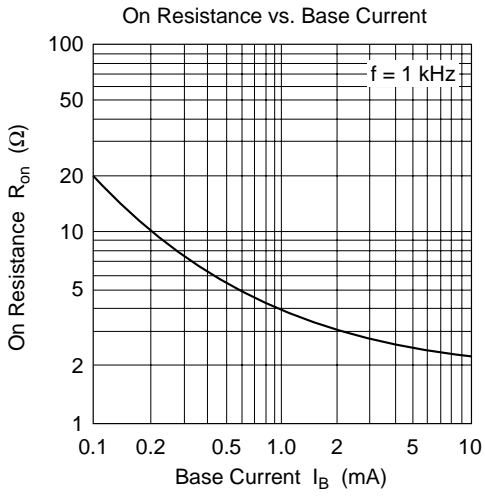
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	12	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

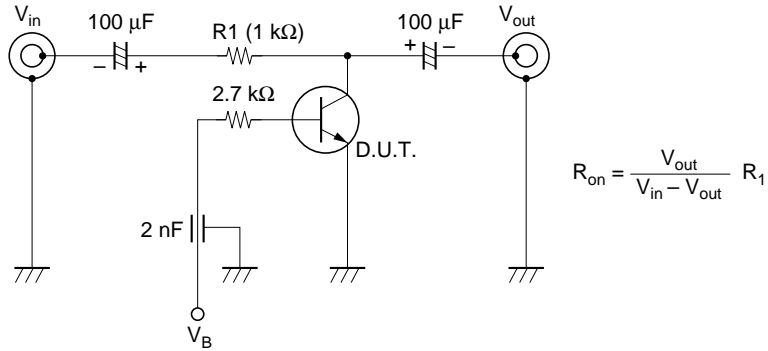
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	12	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 12 V, I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 8 V, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 3 V, I_C = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	70	100	mV	$I_C = 20 mA, I_B = 4 mA$
DC current transfer ratio	h_{FE}	100	250	—		$V_{CE} = 5 V, I_C = 5 mA$
Collector output capacitance	C_{ob}	—	1.0	1.5	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$

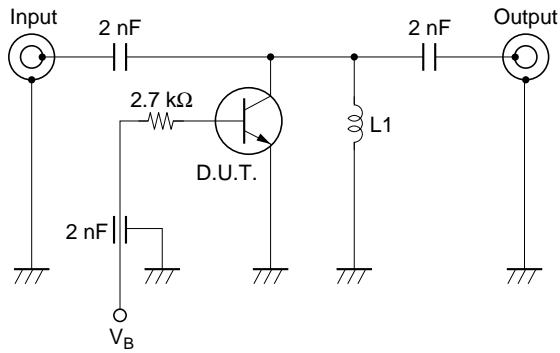




On Resistance Test Circuit

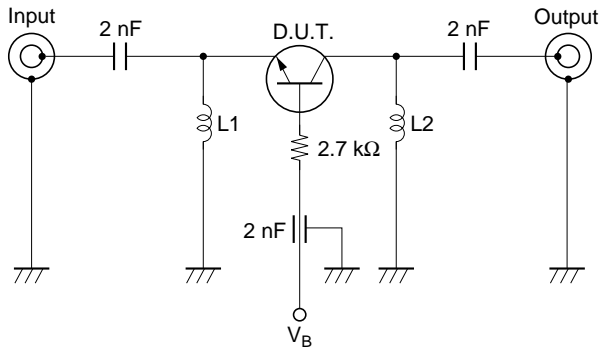


Reduction Test Circuit (Shunt Circuit)



L1 : 3 mm inside dia, φ0.2 mm enameled copper wire, 15 turns

Reduction Test Circuit (Transfer Circuit)

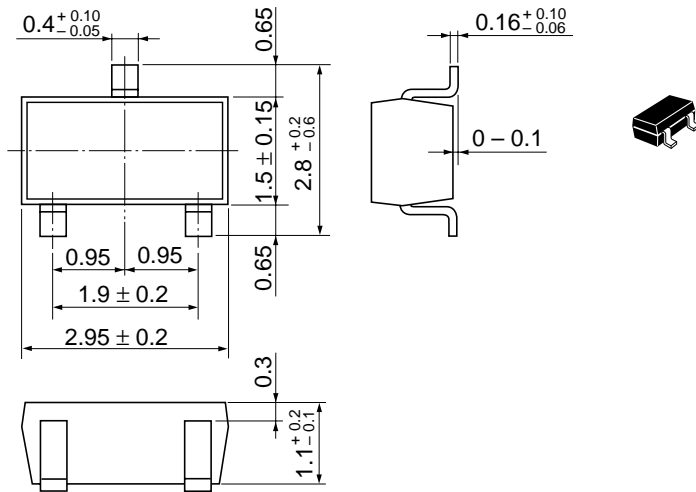


L1, L2 : 3 mm inside dia, φ0.2 mm enameled copper wire, 15 turns

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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